

PROCEEDINGS OF SPIE

Optical and EUV Nanolithography XXXIX

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Editors

23–26 February 2026
San Jose, California, United States

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Published by
SPIE

Volume 13979

Proceedings of SPIE 0277-786X, V. 13979

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

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Please use the following format to cite material from these proceedings:

Author(s), "Title of Paper," in *Optical and EUV Nanolithography XXXIX*, edited by Claire van Lare, Iacopo Mochi, Proc. of SPIE 13979, Seven-digit Article CID Number (DD/MM/YYYY); (DOI URL).

ISSN: 0277-786X

ISSN: 1996-756X (electronic)

ISBN: 9781510699045

ISBN: 9781510699052 (electronic)

Published by

SPIE

P.O. Box 10, Bellingham, Washington 98227-0010 USA

Telephone +1 360 676 3290 (Pacific Time)

SPIE.org

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